

CORRECTED VERSION

(19) World Intellectual Property
Organization
International Bureau



(43) International Publication Date
29 September 2005 (29.09.2005)

PCT

(10) International Publication Number
WO 2005/091370 A1

(51) International Patent Classification⁷: **H01L 27/12**,
21/02, 21/336, 29/786

(21) International Application Number:
PCT/JP2005/005064

(22) International Filing Date: 15 March 2005 (15.03.2005)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
2004-083664 22 March 2004 (22.03.2004) JP

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(81) Designated States (unless otherwise indicated, for every
kind of national protection available): AE, AG, AL, AM,
AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN,
CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI,
GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE,
KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD,
MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG,
PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SM, SY, TJ,
TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA,
ZM, ZW.

(84) Designated States (unless otherwise indicated, for every
kind of regional protection available): ARIPO (BW, GH,
GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM,
ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM),
European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI,
FR, GB, GR, HU, IE, IS, IT, LT, LU, MC, NL, PL, PT, RO,
SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN,
GQ, GW, ML, MR, NE, SN, TD, TG).

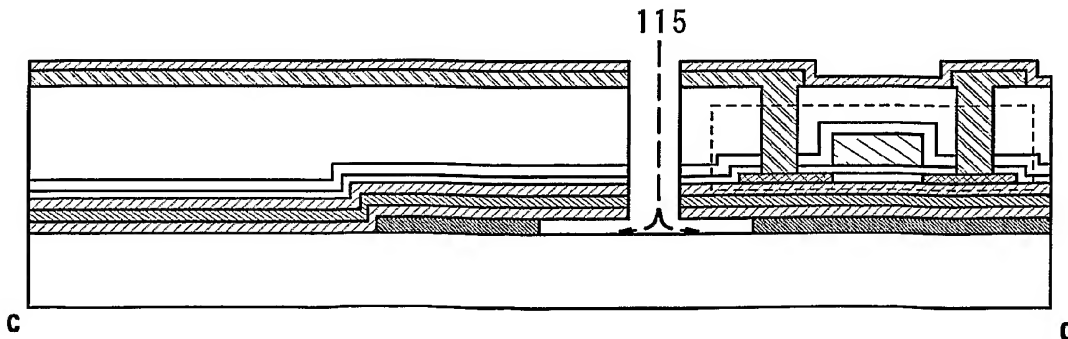
Published:
— with international search report

(48) Date of publication of this corrected version:
24 November 2005

(15) Information about Correction:
see PCT Gazette No. 47/2005 of 24 November 2005, Sec-
tion II

[Continued on next page]

(54) Title: METHOD FOR MANUFACTURING INTEGRATED CIRCUIT



(57) Abstract: A method for separating an integrated circuit formed by a thin film having a novel structure or a method for transfer-
ring the integrated circuit to another substrate, that is, so-called transposing method, has not been proposed. According to the present
invention, in the case that an integrated circuit having a thin film having a novel structure formed over a substrate via a release layer
is separated, the release layer is removed in the state that the thin film integrated circuit is fixated, the thin film integrated circuit is
transposed to a supporting substrate having an adhesion surface, and the thin film integrated circuit is transposed to another substrate
having an adhesion surface with higher strength of adhesion than that of the supporting substrate.

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